

To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SB566(K), 2SB566A(K)

Silicon PNP Triple Diffused

RENESAS

ADE-208-855 (Z)

1st. Edition

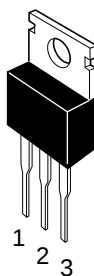
September 2000

Application

Low frequency power amplifier power switching complementary pair with 2SD476(K) and 2SD476A(K)

Outline

TO-220AB



1. Base
2. Collector (Flange)
3. Emitter

2SB566(K), 2SB566A(K)

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings		Unit
		2SB566(K)	2SB566A(K)	
Collector to base voltage	V_{CBO}	-70	-70	V
Collector to emitter voltage	V_{CEO}	-50	-60	V
Emitter to base voltage	V_{EBO}	-5	-5	V
Collector current	I_C	-4	-4	A
Collector peak current	$I_{C(peak)}$	-8	-8	A
Collector power dissipation	P_C^{*1}	40	40	W
Junction temperature	T_j	150	150	°C
Storage temperature	T_{stg}	-55 to +150	-55 to +150	°C

Note: 1. Value at $T_C = 25^\circ\text{C}$.

Electrical Characteristics (Ta = 25°C)

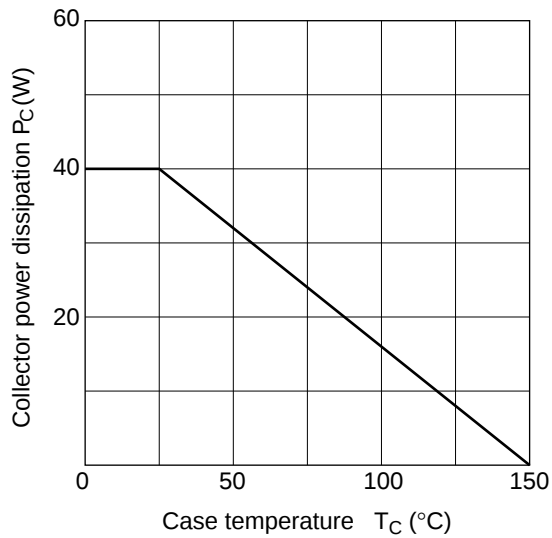
Item	Symbol	2SB566(K)			2SB566A(K)			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	-70	—	—	-70	—	—	V	$I_C = -10\ \mu\text{A}$, $I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-50	—	—	-60	—	—	V	$I_C = -50\ \text{mA}$, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	-5	—	—	V	$I_E = -10\ \mu\text{A}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-1	—	—	-1	μA	$V_{CB} = -50\ \text{V}$, $I_E = 0$
DC current transfer ratio	h_{FE1}^{*1}	60	—	200	60	—	200		$V_{CE} = -4\ \text{V}$, $I_C = -1\ \text{A}$
	h_{FE2}	35	—	—	35	—	—		$V_{CE} = -4\ \text{V}$, $I_C = -0.1\ \text{A}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-1.0	—	—	-1.0	V	$I_C = -2\ \text{A}$, $I_B = -0.2\ \text{A}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	-1.2	—	—	-1.2	V	$I_C = -2\ \text{A}$, $I_B = -0.2\ \text{A}$
Gain bandwidth product	f_T	—	15	—	—	15	—	MHz	$V_{CE} = -4\ \text{V}$, $I_C = -0.5\ \text{A}$
Turn on time	t_{on}	—	0.3	—	—	0.3	—	μs	$V_{CC} = -10.5\ \text{V}$
Turn off time	t_{off}	—	3.0	—	—	3.0	—	μs	$I_C = 10I_{B1} = -10I_{B2} =$
Storage time	t_{stg}	—	2.5	—	—	2.5	—	μs	-0.5 A

Note: 1. The 2SB566(K) and 2SB566A(K) are grouped by h_{FE1} as follows.

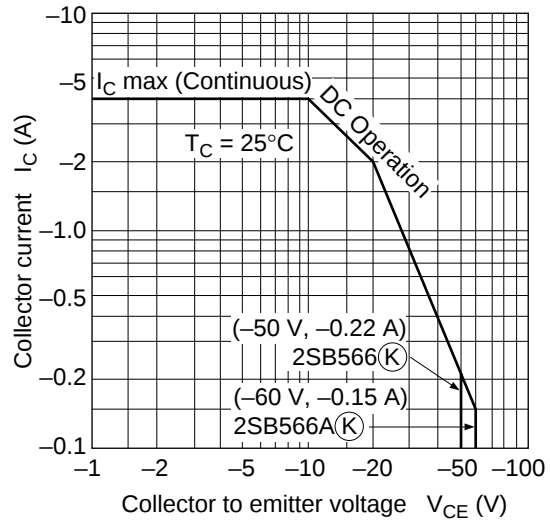
B	C
60 to 120	100 to 200

2SB566(K), 2SB566A(K)

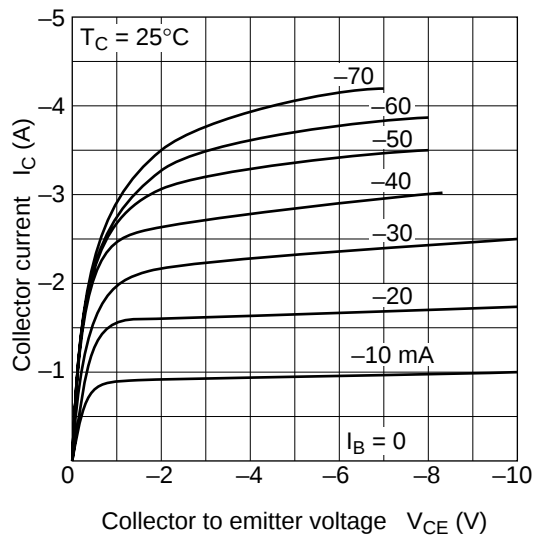
Maximum Collector Dissipation Curve



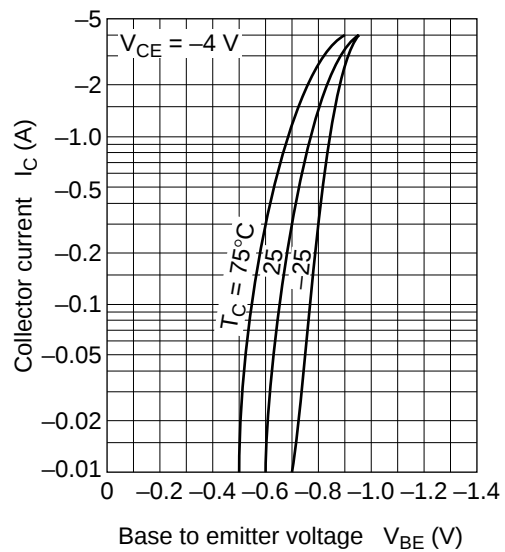
Area Safe Operation



Typical Output Characteristics

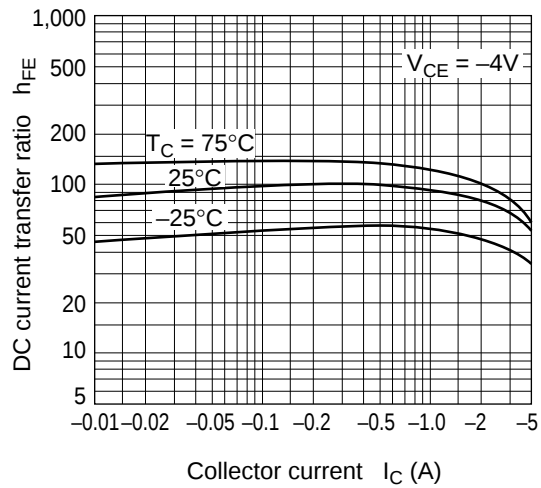


Typical Transfer Characteristics

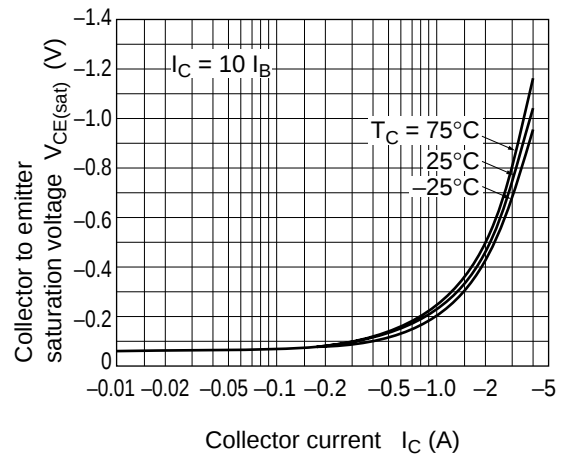


2SB566(K), 2SB566A(K)

DC Current Transfer Ratio
vs. Collector Current



Collector to Emitter Saturation Voltage
vs. Collector Current



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HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100, Japan
Tel: Tokyo (03) 3270-2111
Fax: (03) 3270-5109

For further information write to:

Hitachi America, Ltd.
Semiconductor & IC Div.
2000 Sierra Point Parkway
Brisbane, CA. 94005-1835
U S A
Tel: 415-589-8300
Fax: 415-583-4207

Hitachi Europe GmbH
Electronic Components Group
Continental Europe
Dornacher Straße 3
D-85622 Feldkirchen
München
Tel: 089-9 91 80-0
Fax: 089-9 29 30 00

Hitachi Europe Ltd.
Electronic Components Div.
Northern Europe Headquarters
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA
United Kingdom
Tel: 0628-585000
Fax: 0628-778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 0104
Tel: 535-2100
Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.
Unit 706, North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel: 27359218
Fax: 27306071